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## SPECIAL ISSUE ON LIGHT-EMITTING DIODES

### EDITORIAL

What Is in a Page Charge? . . . . .	<i>S. K. Saha</i>	4
Changes to the Editorial Board . . . . .	<i>D. Verret</i>	5

### GUEST EDITORIAL

Special Issue on Light-Emitting Diodes. . . . .	<i>M. J. Kumar, L. Lunardi, G. Meneghesso, S. J. Pearton, and E. F. Schubert</i>	7
---	--	---

### SPECIAL ISSUE PAPERS

Deep-Ultraviolet Light-Emitting Diodes ( <i>Invited/Review Paper</i> ) . . . . .	<i>M. S. Shur and R. Gaska</i>	12
Recent Advances in ZnO-Based Light-Emitting Diodes ( <i>Invited/Review Paper</i> ) . . . . .	<i>Y.-S. Choi, J.-W. Kang, D.-K. Hwang, and S.-J. Park</i>	26
Ohmic-Contact Technology for GaN-Based Light-Emitting Diodes: Role of P-Type Contact ( <i>Invited/Review Paper</i> ) . . . . .	<i>J. O Song, J.-S. Ha, and T.-Y. Seong</i>	42
Design Criteria for Near-Ultraviolet GaN-Based Light-Emitting Diodes ( <i>Invited Paper</i> ) . . . . .	<i>S. Chiaria, E. Furno, M. Goano, and E. Bellotti</i>	60
Nitride Nanocolumns for the Development of Light-Emitting Diode ( <i>Invited Paper</i> ) . . . . .	<i>T.-Y. Tang, C.-H. Lin, Y.-S. Chen, W.-Y. Shiao, W.-M. Chang, C.-H. Liao, K.-C. Shen, C.-C. Yang, M.-C. Hsu, J.-H. Yeh, and T.-C. Hsu</i>	71
High-Power and High-Efficiency InGaN-Based Light Emitters ( <i>Invited Paper</i> ) . . . . .	<i>A. Laubsch, M. Sabathil, J. Baur, M. Peter, and B. Hahn</i>	79
Nonpolar and Semipolar III-Nitride Light-Emitting Diodes: Achievements and Challenges ( <i>Invited Paper</i> ) . . . . .	<i>H. Masui, S. Nakamura, S. P. DenBaars, and U. K. Mishra</i>	88
High-Efficiency Blue Emitting Phosphorescent OLEDs ( <i>Invited Paper</i> ) . . . . .	<i>N. Chopra, J. Lee, J. Xue, and F. So</i>	101
A Review on the Physical Mechanisms That Limit the Reliability of GaN-Based LEDs . . . . .	<i>M. Meneghini, A. Tazzoli, G. Mura, G. Meneghesso, and E. Zanoni</i>	108
Electrostatic Reliability Characteristics of GaN Flip-Chip Power Light-Emitting Diodes With Metal-Oxide-Silicon Submount . . . . .	<i>L.-B. Chang, K.-L. Chiang, H.-Y. Chang, M.-J. Jeng, C.-Y. Yen, C.-C. Lin, Y.-H. Chang, M.-J. Lai, Y.-L. Lee, and T.-W. Soong</i>	119
Blue Organic LEDs With Improved Power Efficiency. . . . .	<i>H. M. Zhang, W. C. H. Choy, and K. Li</i>	125

(Contents Continued on Page 2)



---

<i>n</i> -ZnO/ <i>n</i> -GaAs Heterostructured White Light-Emitting Diode: Nanoscale Interface Analysis and Electroluminescence Studies . . . . .	<i>S. T. Tan, J. Zhao, S. Iwan, X. W. Sun, X. Tang, J. Ye, M. Bosman, L. Tang, G.-Q. Lo, and K. L. Teo</i>	129
GaN-Based LEDs With AZO:Y Upper Contact. . . . .	<i>P. H. Chen, W. C. Lai, L.-C. Peng, C. H. Kuo, C.-L. Yeh, J. K. Sheu, and C. J. Tun</i>	134
III-Nitride-Based Light-Emitting Diodes With GaN Micropillars Around Mesa and Patterned Substrate . . . . .	<i>L.-C. Peng, W.-C. Lai, M.-N. Chang, T.-H. Hsueh, S.-C. Shei, and J.-K. Sheu</i>	140
Polymer-MEMS-Based Optoelectronic Display . . . . .	<i>Y. D. Gokdel, A. O. Sevim, S. Mutlu, and A. D. Yalcinkaya</i>	145
Laboratory Thin-Film Encapsulation of Air-Sensitive Organic Semiconductor Devices . . . . .	<i>S. P. Subbarao, M. E. Bahlke, and I. Kymissis</i>	153
Comparison of InGaN-Based LEDs Grown on Conventional Sapphire and Cone-Shape-Patterned Sapphire Substrate . . . . .	<i>J.-H. Lee, D.-Y. Lee, B.-W. Oh, and J.-H. Lee</i>	157
Electronic Structure of InN/GaN Quantum Dots: Multimillion-Atom Tight-Binding Simulations . . . . .	<i>S. Ahmed, S. Islam, and S. Mohammed</i>	164
LED-Based Optical Device for Chronic <i>In Vivo</i> Cerebral Blood Volume Measurement . . . . .	<i>M. P. Cox, H. Ma, M. E. Bahlke, J. H. Beck, T. H. Schwartz, and I. Kymissis</i>	174
Impact of Trapped Charge and Interface Defects on the Degradation of the Optical and Electrical Characteristics in NPD/Alq <sub>3</sub> OLEDs. . . . .	<i>A. Pinato, A. Cester, M. Meneghini, N. Wrachien, A. Tazzoli, S. Xia, V. Adamovich, M. S. Weaver, J. J. Brown, E. Zanoni, and G. Meneghesso</i>	178

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REGULAR PAPERS

**Compound Semiconductor Devices**

Performance of High-Reliability and High-Linearity InGaP/GaAs HBT PAs for Wireless Communication. . . . .	<i>M.-C. Tu, H.-Y. Ueng, and Y.-C. Wang</i>	188
---	---	-----

**Molecular and Organic Devices**

Structural Analysis on Organic Thin-Film Transistor With Device Simulation . . .	<i>C.-H. Shim, F. Maruoka, and R. Hattori</i>	195
Noise-Margin Analysis for Organic Thin-Film Complementary Technology . . . . .	<i>D. Bode, C. Rolin, S. Schols, M. Debuquoy, S. Steudel, G. H. Gelinck, J. Genoe, and P. Heremans</i>	201

**Nanoelectronics**

Current–Voltage Characteristics of Graphane p-n Junctions . . . . .	<i>B. Gharekhanlou and S. Khorasani</i>	209
---	---	-----

**Optoelectronics Display and Imaging**

Study on Pulse Waveforms for Improving Voltage Margin and Luminous Efficacy in an AC Plasma Display Panel Having Auxiliary Electrodes . . . . .	<i>S.-M. Lee, C. S. Choi, C. Jang, and K. C. Choi</i>	215
Sub-1-V CMOS Image Sensor Using Time-Based Readout Circuit . . . . .	<i>K. Cho, D. Lee, J. Lee, and G. Han</i>	222

**Reliability**

NBTI Lifetime Prediction and Kinetics at Operation Bias Based on Ultrafast Pulse Measurement . . . . .	<i>Z. Ji, L. Lin, J. F. Zhang, B. Kaczer, and G. Groeseneken</i>	228
Improvement of Negative Bias Temperature Instability by Stress Proximity Technique . . . . .	<i>J. B. Yang, T. P. Chen, Y. Gong, S. S. Tan, C. M. Ng, and L. Chan</i>	238

**Review Articles**

Electronic Microsystems for Handling of Rare Cells . . . . .	<i>M. Bocchi, E. F. Scarselli, and R. Guerrieri</i>	244
--	---	-----

**Silicon Devices**

Electrical Modeling and Characterization of Through Silicon via for Three-Dimensional ICs. . . . .	<i>G. Katti, M. Stucchi, K. De Meyer, and W. Dehaene</i>	256
Global Modeling Strategy of Parasitic Coupled Currents Induced by Minority-Carrier Propagation in Semiconductor Substrates . . . . .	<i>F. Lo Conte, J.-M. Sallese, M. Pastre, F. Krummenacher, and M. Kayal</i>	263
The Effect of Random Dopant Fluctuation on Specific Contact Resistivity . . . . .	<i>R. A. Vega, V. C. Lee, and T.-J. King Liu</i>	273
Low-Temperature Formation of High-Quality GeO <sub>2</sub> Interlayer for High- $\kappa$ Gate Dielectrics/Ge by Electron-Cyclotron-Resonance Plasma Techniques. . . . .	<i>Y. Fukuda, Y. Yazaki, Y. Otani, T. Sato, H. Toyota, and T. Ono</i>	282
Energy and Spatial Distributions of Electron Traps Throughout SiO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> Stacks as the IPD in Flash Memory Application . . . . .	<i>X. F. Zheng, W. D. Zhang, B. Govoreanu, D. Ruiz Aguado, J. F. Zhang, and J. Van Houdt</i>	288
A Self-Aligned InGaAs HEMT Architecture for Logic Applications . . . . .	<i>N. Waldron, D.-H. Kim, and J. A. del Alamo</i>	297
Novel Multilayer Dipoles for Wireless Inter-/Intraconnects . . . . .	<i>Q. Wu, R. Jin, and J. Geng</i>	305

---

---

Three-Terminal Probe Reconfigurable Phase-Change Material Switches . . . . .	<i>H. Lo, E. Chua, J. C. Huang, C. C. Tan, C.-Y. Wen, R. Zhao, L. Shi, C. T. Chong, J. Paramesh, T. E. Schlesinger, and J. A. Bain</i>	312
Data Retention and Program/Erase Sensitivity to the Array Background Pattern in Deca-nanometer NAND Flash Memories . . . . .	<i>C. Monzio Compagnoni, A. Ghetti, M. Ghidotti, A. S. Spinelli, and A. Visconti</i>	321

**Solid-State Device Phenomena**

A 65-nm High-Frequency Low-Noise CMOS-Based RF SoC Technology . . . . .	<i>D. Yang, Y. Ding, and S. Huang</i>	328
Effective Mobility in Nanowire FETs Under Quasi-Ballistic Conditions . . . . .	<i>E. Gnani, A. Gnudi, S. Reggiani, and G. Baccarani</i>	336

**Solid-State Power and High Voltage**

Thermal Accumulation Effects on the Transient Temperature Responses in LDMOSFETs Under the Impact of a Periodic Electromagnetic Pulse. . . . .	<i>Z. Ren, W.-Y. Yin, Y.-B. Shi, and Q. H. Liu</i>	345
--	--	-----

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**BRIEFS**

Effects of Threading Dislocations on AlGaIn/GaN High-Electron Mobility Transistors . . . . .	<i>F. A. Marino, N. Faralli, T. Palacios, D. K. Ferry, S. M. Goodnick, and M. Saraniti</i>	353
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About the Cover: DUV light distribution from LEDs with ball lens (left) and flat lens (right) from “Deep-Ultraviolet Light-Emitting Diodes,” by M. S. Shur and R. Gaska.